| PCN Numb   | 20230224000.2       |            |              |                |           | PCN Date:  |                                 |                     | February 24,<br>2023 |                  |  |
|--|---------------------|------------|--------------|----------------|-----------|------------|---------------------------------|---------------------|----------------------|------------------|--|
| Title:Qualification of DMOS6 as an additional Fab site and additional wafer Probe site<br>(CDAT-PR) options for select devices |                     |            |              |                |           |            |                                 |                     |                      | afer Probe site  |  |
| Customer   | Contact:            | PCN M      | lanager      |                |           |            | Dept:                           |                     |                      | Quality Services |  |
| Proposed 1 <sup>st</sup> Ship Date: Aug 22   |                     |            |              | 7, 2023        |           |            | Sample requests accepted until: |                     |                      | Mar 27, 2023*    |  |
| *Sample re   | quests receive      | d after Ma | rch 2        | 7, 2023        | 8 will no | ot be su   | рро                             | rted                |                      |                  |  |
| Change Ty  | pe:                 |            |              |                |           |            |                                 |                     |                      |                  |  |
|  | bly Site            |            |              | Design         |           |            |                                 | Wafer Bump Site     |                      |                  |  |
| Assem  | bly Process         |            |              | Data Sh        | eet       |            |                                 | Wafer Bump Material |                      |                  |  |
|  | bly Materials       |            |              | Part nur       | nber cl   | nange      |                                 | Wafer Bump Process  |                      |                  |  |
|  | nical Specificat    |            | 🛛 Test Site  |                |           |            |                                 | Wafer Fab Site      |                      |                  |  |
|  | g/Shipping/Lat      | beling     | Test Process |                |           |            | Wafer Fab Materials             |                     |                      |                  |  |
|  |                     |            |              |                |           |            |                                 |                     | Wafer                | Fab Process      |  |
| PCN Details  |                     |            |              |                |           |            |                                 |                     |                      |                  |  |
| _  | n of Change:        |            |              |                |           |            |                                 |                     |                      |                  |  |
| Texas Instruments is pleased to announce the qualification of its DMOS6 fabrication facility as                                |                     |            |              |                |           |            |                                 |                     |                      |                  |  |
| an additional Wafer Fab source and CDAT-PR as an additional probe site options for the selected                                |                     |            |              |                |           |            |                                 |                     |                      |                  |  |
| devices listed in the "Product Affected" section.  |                     |            |              |                |           |            |                                 |                     |                      |                  |  |
|  | Additional Fab Site |            |              |                |           |            |                                 |                     |                      |                  |  |
| Current Fab Process  |                     |            |              | fer            | Add       | Additional |                                 | Process             |                      | Wafer            |  |
| Site   | Site                |            |              |                | Fab Site  |            |                                 |                     |                      | Diameter         |  |
| RFAB LBC9  |                     |            | 300 mm       |                |           | 10S6       | OS6 LBC9                        |                     | LBC9                 | 300mm            |  |
| Probe site o   | changes are as      | follows:   |              |                |           |            |                                 |                     |                      |                  |  |
| l l  | Current P           | robe Site  |              | New Probe Site |           |            |                                 |                     |                      |                  |  |
|  | CLAF                |            | CDAT-PR      |                |           |            |                                 |                     |                      |                  |  |

Test coverage, insertions, conditions will remain consistent with current testing.

Reason for Change: Continuity of Supply

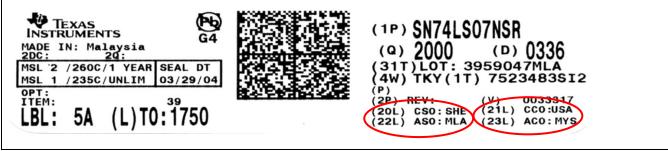
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative): None

Changes to product identification resulting from this PCN:

## Fab Site Information:

| Chip Site | Chip Site Origin Code<br>(20L) | Chip Site Country Code<br>(21L) | Chip Site City    |  |
|-----------|--------------------------------|---------------------------------|-------------------|--|
| RFAB      | RFB                            | USA                             | Richardson        |  |
| DMOS6     | DM6                            | USA                             | <b>Richardson</b> |  |

Sample product shipping label (not actual product label)



**Product Affected:** 

| TPS25831QCWRHBRQ1 | TPS25840QCWRHBRQ1 |
|-------------------|-------------------|
| TPS25832QCWRHBRQ1 | TPS25842QCWRHBRQ1 |
| TPS25833QCWRHBRQ1 | TPS25846QCWRHBRQ1 |
|                   | TPS25832QCWRHBRQ1 |

## Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Approved 18-Jan-2023

## **Qualification Results**

Data Displayed as: Number of lots / Total sample size / Total failed

|            |              |   |                   |             | Data D                                       | ispiay   | ed as         | s: Number   | ot lots /  | lotal sam   | pie size  | / Total faile                                    | a   |   |   |
|------------|--------------|---|-------------------|-------------|--|--|---------------|---|--|---|---|--|---|---|---|
| Туре       |              | Test Spec   | Min<br>Lot        | SS /<br>Lot | Test Name                                    | Condition  | Duration      | Qual Device:<br>TPS25831QCWRHBRQ1                   | QBS Reference:<br>DRV8873SPWPRQ1   | QBS Reference:<br>TPS25831QWRHBRQ1                  | QBS Reference:<br>DRV8703QRHBRQ1                    | QBS Reference:<br>PTPS38FPUENGDSKRQ1             | QBS Reference:<br>TPS25831QWRHBRQ1                  | QBS Reference:<br>TPS25830QWRHBRQ1                  | QBS Reference:<br>TPS25831QWRHBRQ1                  |
| Test Group | A - Accelar  | atad Environm                                     | Qty<br>ent Stress |             | <b></b>                                      | l  |               | TP 32.021 Q CHIKING Y                               | <u>on the set of the set</u> |   |   |  |   | Translation (Translation)                           | TP SESSION WITH MUNICIPAL                           |
| Test Group | A - Acceler  | JEDEC J-  | ent stress        | Tests       |  |  |               |   |  |   |   |  |   |   |   |
| PC         | A1           | STD-020<br>JESD22-<br>A113                        | 3                 | 77          | Preconditioning                              | MSL2 260C  | 1 Step        | 10/0  | -  | 3/0/0   | 3/0/0   | -  | 1/0/0   | 10/0  | 3/0/0   |
| PC         | A1           | JEDEC J-<br>STD-020<br>JESD22-<br>A113            | 3                 | 77          | Preconditioning                              | MSL3 260C  | 1 Step        |   | 3/0/0  | -   | -   |  | -   |   |   |
| HAST       | A2           | JEDEC<br>JESD22-<br>A110                          | 3                 | 77          | Biased HAST                                  | 130C/85%RH                                       | 96 Hours      | -   | 3/231/0  | 3/231/0   | 3/231/0   | 3/231/0  | -   | -   | 3/231/0   |
| AC/UHAST   | A3           | JEDEC<br>JESD22-<br>A102/JEDEC<br>JESD22-<br>A118 | 3                 | 77          | Autoclave                                    | 121C/15psig                                      | 96 Hours      | -   |  | 3/231/0   | -   |  | -   | -   | 3/231/0   |
| AC/UHAST   | A3           | JEDEC<br>JESD22-<br>A102/JEDEC<br>JESD22-<br>A118 | 3                 | 77          | Unbiased HAST                                | 130C/85%RH                                       | 96 Hours      | -   | 3/231/0  | -   | 3/231/0   | 3/231/0  | -   | -   | -   |
| тс         | A4           | JEDEC<br>JESD22-<br>A104 and<br>Appendix 3        | 3                 | n           | Temperature<br>Cycle                         | -65C/150C  | 500<br>Cycles | 1/77/0  |  | -   | 3/231/0   | 3/231/0  | -   | 1/77/0  |   |
| тс-вр      | A4           | MIL-STD883<br>Method 2011                         | 1                 | 5           | Post Temp<br>Cycle Bond Pull                 | -  |               | 1/5/0   | -  | -   | 3/15/0  | 1/5/0  | -   | 1/5/0   | -   |
| HTSL       | A6           | JEDEC<br>JESD22-<br>A103                          | 1                 | 45          | High<br>Temperature<br>Storage Life          | 150C   | 1000<br>Hours | -   | 3/135/0  | -   | 3/135/0   | 3/135/0  | -   | -   | 3/135/0   |
| HTSL       | A6           | JEDEC<br>JESD22-<br>A103                          | 1                 | 45          | High<br>Temperature<br>Storage Life          | 175C   | 500<br>Hours  |   |  | 3/135/0   | -   | -  | -   |   |   |
| Test Group | B - Acceler  | rated Lifetime S                                  | imulation         | Tests       |  |  |               |   |  |   |   |  |   |   |   |
| HTOL       | 81           | JEDEC<br>JESD22-<br>A108                          | 1                 | 77          | Life Test                                    | 125C   | 1000<br>Hours | -   | 3/231/0  | 3/231/0   | -   | -  | -   | -   | 3/231/0   |
| ELFR       | B2           | AEC Q100-<br>008                                  | 1                 | 77          | Early Life<br>Failure Rate                   | 125C   | 48 Hours      |   | 3/2400/0   | 1/800/0   | -   | 3/2400/0   | -   | -   | 1/800/0   |
| Test Group | C - Packag   | e Assembly Inte                                   | egrity Test       | 8           |  |  |               |   |  |   |   |  |   |   |   |
| WBS        | C1           | AEC Q100-<br>001                                  | 1                 | 30          | Wire Bond<br>Shear                           | Minimum of 5<br>devices, 30<br>wires<br>Cpk>1.67 | Wires         | 1/30/0  | 3/90/0   | -   | 3/90/0  | 3/90/0   | -   | -   | 3/90/0  |
| WBP        | C2           | MIL-STD883<br>Method 2011                         | 1                 | 30          | Wire Bond Pull                               | Minimum of 5<br>devices, 30<br>wires<br>Cpk>1.67 | Wires         | 1/30/0  | 3/90/0   | -   | 3/90/0  | 3/90/0   | -   | -   | 3/90/0  |
| SD         | СЗ           | JEDEC J-<br>STD-002                               | 1                 | 15          | PB Solderability                             | >95% Lead<br>Coverage                            | -             | 1/15/0  | 1/15/0   | -   | 1/15/0  | 1/15/0   | 1/15/0  | •   | 1/15/0  |
| SD         | C3           | JEDEC J-<br>STD-002                               | 1                 | 15          | PB-Free<br>Solderability                     | >95% Lead<br>Coverage                            | -             | 1/15/0  | 1/15/0   | -   | 1/15/0  | 1/15/0   | 1/15/0  | -   | 1/15/0  |
| PD         | C4           | JEDEC<br>JESD22-<br>B100 and<br>B108              | 1                 | 10          | Physical<br>Dimensions                       | Cpk>1.67   | -             | 1/10/0  | 3/30/0   | 3/30/0  | 3/30/0  | 3/30/0   | -   | -   | 3/30/0  |
| Test Group | D - Die Fal  | prication Reliab                                  | ility Tests       |             |  |  |               |   |  |   |   |  |   |   |   |
| ЕМ         | D1           | JESD61  | -                 |             | Electromigration                             | -  | -             | Completed Per Process<br>Technology<br>Requirements | Completed Per<br>Process Technology<br>Requirements  | Completed Per Process<br>Technology<br>Requirements | Completed Per<br>Process Technology<br>Requirements | Completed Per Process<br>Technology Requirements | Completed Per Process<br>Technology<br>Requirements | Completed Per Process<br>Technology<br>Requirements | Completed Per Process<br>Technology<br>Requirements |
| TDDB       | D2           | JESD35  |                   |             | Time<br>Dependent<br>Dielectric<br>Breakdown | -  |               | Completed Per Process<br>Technology<br>Requirements | Completed Per<br>Process Technology<br>Requirements  | Completed Per Process<br>Technology<br>Requirements | Completed Per<br>Process Technology<br>Requirements | Completed Per Process<br>Technology Requirements | Completed Per Process<br>Technology<br>Requirements | Completed Per Process<br>Technology<br>Requirements | Completed Per Process<br>Technology<br>Requirements |
| нсі        | D3           | JESD60 & 28                                       | -                 |             | Hot Carrier<br>Injection                     | -  | -             | Completed Per Process<br>Technology<br>Requirements | Completed Per<br>Process Technology<br>Requirements  | Completed Per Process<br>Technology<br>Requirements | Completed Per<br>Process Technology<br>Requirements | Completed Per Process<br>Technology Requirements | Completed Per Process<br>Technology<br>Requirements | Completed Per Process<br>Technology<br>Requirements | Completed Per Process<br>Technology<br>Requirements |
| NBTI       | D4           | -   | -                 | -           | Negative Bias<br>Temperature<br>Instability  | -  |               | Completed Per Process<br>Technology<br>Requirements | Completed Per<br>Process Technology<br>Requirements  | Completed Per Process<br>Technology<br>Requirements | Completed Per<br>Process Technology<br>Requirements | Completed Per Process<br>Technology Requirements | Completed Per Process<br>Technology<br>Requirements | Completed Per Process<br>Technology<br>Requirements | Completed Per Process<br>Technology<br>Requirements |
| SM         | D5           | -   |                   | -           | Stress<br>Migration                          | -  |               | Completed Per Process<br>Technology<br>Requirements | Completed Per<br>Process Technology<br>Requirements  | Completed Per Process<br>Technology<br>Requirements | Completed Per<br>Process Technology<br>Requirements | Completed Per Process<br>Technology Requirements | Completed Per Process<br>Technology<br>Requirements | Completed Per Process<br>Technology<br>Requirements | Completed Per Process<br>Technology<br>Requirements |
| Test Group | E - Electric | al Verification                                   | Tests             |             |  |  |               |   |  |   |   |  |   |   |   |
| ESD        | E2           | AEC Q100-<br>002                                  | 1                 | 3           | ESD HBM                                      | -  | 2000<br>Volts | -   | 1/3/0  | -   | 1/3/0   | 1/3/0  | -   | -   | -   |
| ESD        | E2           | AEC Q100-<br>002                                  | 1                 | 3           | ESD HBM                                      | -  | 4000<br>Volts | -   | -  | -   | -   | -  | -   | 1/3/0   | 1/3/0   |
| ESD        | E3           | AEC Q100-<br>011                                  | 1                 | 3           | ESD CDM                                      | -  | 1000<br>Volts |   |  | -   |   |  | -   | -   | 1/3/0   |
| ESD        | E3           | AEC Q100-<br>011                                  | 1                 | 3           | ESD CDM                                      | -  | 1500<br>Volts |   |  |   |   | -  |   | 1/3/0   | -   |
| ESD        | E3           | AEC Q100-<br>011                                  | 1                 | 3           | ESD CDM                                      |  | 500 Volts     |   | 1/3/0  | -   | 1/3/0   | 1/3/0  | -   |   |   |
| LU         | E4           | AEC Q100-<br>004                                  | 1                 | 6           | Latch-Up                                     | Per AEC<br>Q100-004                              | -             | -   | 1/6/0  | 1/6/0   | 1/6/0   | 1/6/0  | -   | 1/6/0   | 1/6/0   |
| ED         | E5           | AEC Q100-<br>009                                  | 3                 | 30          | Electrical<br>Distributions                  | Cpk>1.67<br>Room, hot,<br>and cold               | -             | 1/30/0  | 3/90/0   | 3/90/0  | 3/90/0  | 3/90/0   | 1/30/0  | 1/30/0  | 3/90/0  |
|            |              |   |                   |             |  | 1  | 1             |   |  | 1   | 1   | 1  | 1   |   |   |

Texas Instruments Incorporated

TI Information - Selective Disclosure

PCN# 20230224000.2

| TPS25830QCWRHBRQ1 | TPS25846QCWRHBRQ1 |
|-------------------|-------------------|
| TPS25840QCWRHBRQ1 | TPS25833QCWRHBRQ1 |
| TPS25831QCWRHBRQ1 | SN1805032CRHBR    |
| TPS25842QCWRHBRQ1 | SN2004001CRHBR    |
| TPS25832QCWRHBRQ1 |                   |

QBS: Qual By Similarity

Qual Device TPS25831QCWRHBRQ1 is qualified at MSL2 260C

Each product in the family passed yield analysis

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C Grade 1 (or Q): -40C to +125C Grade 2 (or T): -40C to +105C

Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com

ZVEI ID reference: SEM-PW-13, SEM-TF-01

For questions regarding this notice, e-mails can be sent to the contact below or your local Field Sales Representative.

| Location                  | E-Mail                        |  |  |  |  |  |
|---------------------------|-------------------------------|--|--|--|--|--|
| WW Change Management Team | PCN ww admin team@list.ti.com |  |  |  |  |  |

## IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disdaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale (<u>www.ti.com/legal/termsofsale.html</u>) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.